

SMD Efficient Fast Recovery Rectifier

CEFB101-G Thru CEFB105-G (RoHS Device)

Reverse Voltage: 50 ~ 600 Volts

Forward Current: 1.0 Amp

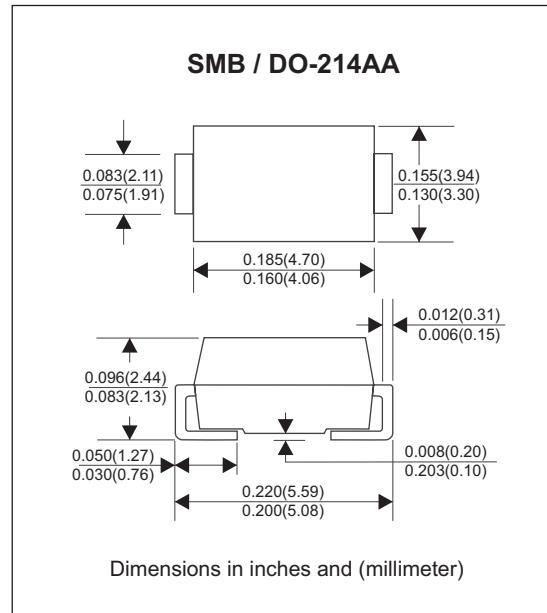


Features:

- Ideal for surface mount applications
- Easy pick and place
- Plastic package has Underwriters Lab. flammability classification 94V-0.
- Super fast recovery time for high efficient
- Built-in strain relief
- Low forward voltage drop

Mechanical Data:

- Case: JEDEC DO-214AA molded plastic
- Terminals: solderable per MIL-STD-750, method 2026
- Polarity: Color band denotes cathode end
- Approx. Weight: 0.063 gram



Maximum Ratings and Electrical Characteristics:

Parameter	Symbol	CEFB101-G	CEFB102-G	CEFB103-G	CEFB104-G	CEFB105-G	Unit
Max. Repetitive Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	V
Max. DC Blocking Voltage	V_{DC}	50	100	200	400	600	V
Max. RMS Voltage	V_{RMS}	35	70	140	280	420	V
Peak Surge Forward Current 8.3ms single half sine-wave superimposed on rate load (JEDEC method)	I_{FSM}			30			A
Max. Average Forward Current	I_o			1.0			A
Max. Instantaneous Forward Voltage at 1.0A	V_F		0.875		1.1	1.25	V
Reverse recovery time	T_{rr}		25		35	50	nS
Max. DC Reverse Current at Rated DC Blocking Voltage $T_a=25^\circ\text{C}$ $T_a=100^\circ\text{C}$	I_R			5.0 200			uA
Max. Thermal Resistance (Note1)	$R_{\theta JL}$			13			°C/W
Max. Operating Junction Temperature	T_j			150			°C
Storage Temperature	T_{STG}			-55 to +150			°C

Note1: Thermal resistance from junction to lead mounted on PCB with 8.0mmx8.0mm² copper pad areas.

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Rating and Characteristic Curves (CEFB101-G Thru CEFB105-G)

Fig.1- Reverse Characteristics

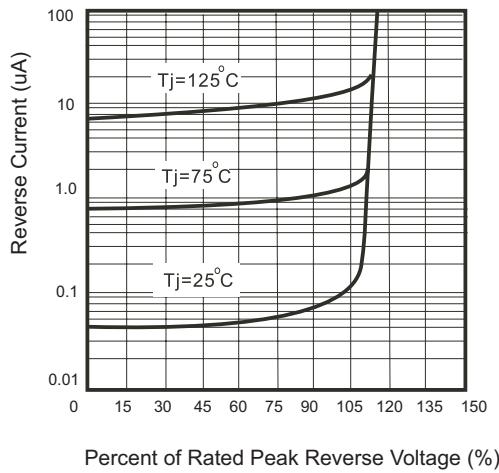


Fig.2 - Forward Characteristics

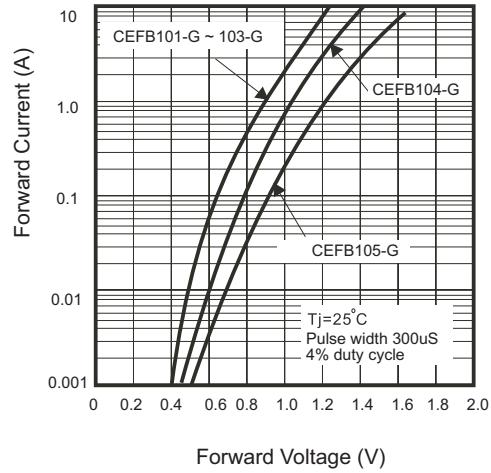


Fig. 3 - Junction Capacitance

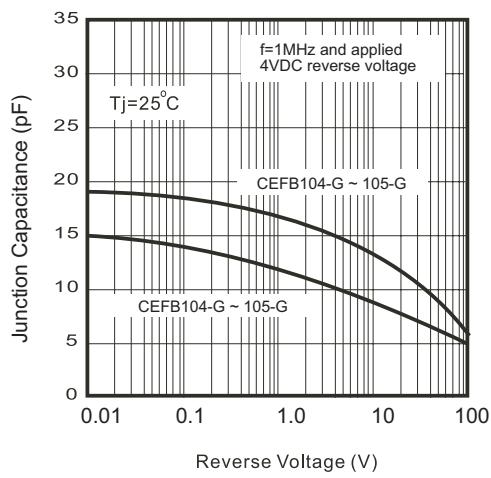


Fig.4 - Non Repetitive Forward Surge Curve

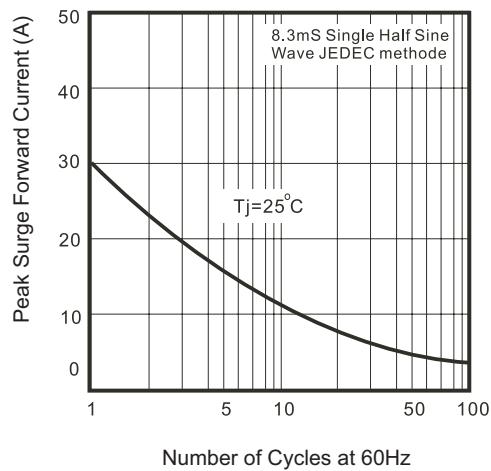
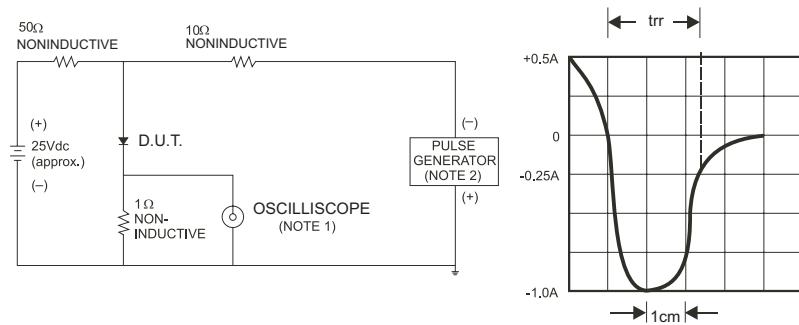


Fig.5 - Test Circuit Diagram and Reverse Recovery Time Characteristics



SET TIME BASE FOR
50 / 10ns / cm

Fig. 6 - Current Derating Curve

